

NP29N06QUK

60 V – 30 A – Dual N-channel Power MOS FET
 Application: Automotive

R07DS1331EJ0100
 Rev.1.00
 Mar 28, 2016


Description

NP29N06QUK is a dual N-channel MOS Field Effect Transistor designed for high current switching applications.

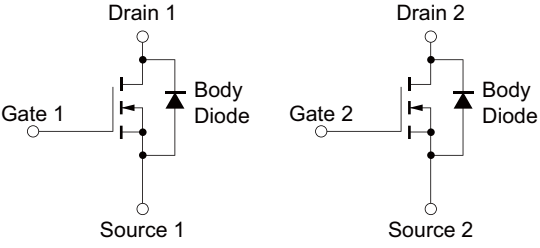
Features

- Super low on-state resistance
 — $R_{DS(on)} = 21 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 15 \text{ A)}$
- Low C_{iss} : $C_{iss} = 1000 \text{ pF TYP. (} V_{DS} = 25 \text{ V)}$
- Designed for automotive application and AEC-Q101 qualified
- Small size package 8-pin HSON dual

Outline



8-pin HSON dual



Equivalent circuit

Remark: Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

Ordering Information

Part No.	Lead Plating	Packing		Package
NP29N06QUK-E1-AY *1	Pure Sn (Tin)	Tape 2500 p/reel	Taping (E1 type)	8-pin HSON dual
NP29N06QUK -E2-AY *1			Taping (E2 type)	

Note: *1. Pb-free (This product does not contain Pb in the external electrode)

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to Source Voltage ($V_{GS} = 0\text{ V}$)	V_{DSS}	60	V
Gate to Source Voltage ($V_{DS} = 0\text{ V}$)	V_{GSS}	± 20	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$) ^{*4}	$I_{D(DC)}$	± 30	A
Drain Current (pulse) ^{*1, 4}	$I_{D(pulse)}$	± 60	A
Total Power Dissipation ($T_C = 25^\circ\text{C}$) ^{*4}	P_{T1}	44	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$) ^{*2, 4}	P_{T2}	1.0	W
Channel Temperature	T_{ch}	175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +175	$^\circ\text{C}$
Repetitive Avalanche Current ^{*3}	I_{AR}	15	A
Repetitive Avalanche Energy ^{*3}	E_{AR}	23	mJ

Thermal Resistance

Channel to Case Thermal Resistance	$R_{th(ch-C)}$	3.37	$^\circ\text{C/W}$
Channel to Ambient Thermal Resistance ^{*2}	$R_{th(ch-A)}$	150	$^\circ\text{C/W}$

Notes: *1. $T_C = 25^\circ\text{C}$, $PW \leq 10\ \mu\text{s}$, Duty Cycle $\leq 1\%$

*2. Mounted on glass epoxy substrate of 40 mm \times 40 mm \times 1.6 mm with 4% copper area (35 μm)

*3. $R_G = 25\ \Omega$, $V_{GS} = 20\text{ V} \rightarrow 0\text{ V}$

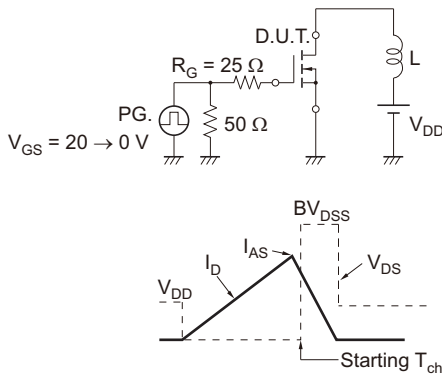
*4. One channel operation

Electrical Characteristics ($T_A = 25^\circ\text{C}$)

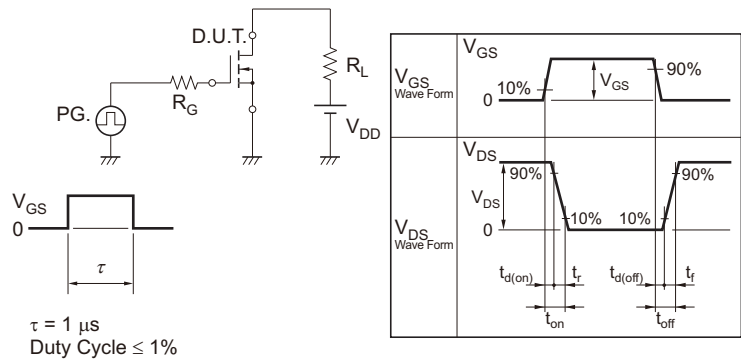
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero Gate Voltage Drain Current	I_{DSS}			1	μA	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$
Gate Leakage Current	I_{GSS}			± 100	nA	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$
Gate to Source Threshold Voltage	$V_{GS(th)}$	2.0	3.0	4.0	V	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$
Forward Transfer Admittance *1	$ y_{fs} $	10	20		S	$V_{DS} = 5\text{ V}, I_D = 15\text{ A}$
Drain to Source On-state Resistance *1	$R_{DS(on)1}$		16.2	21	m Ω	$V_{GS} = 10\text{ V}, I_D = 15\text{ A}$
Input Capacitance	C_{iss}		1000	1500	pF	$V_{DS} = 25\text{ V},$ $V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$
Output Capacitance	C_{oss}		150	230	pF	
Reverse Transfer Capacitance	C_{rss}		70	130	pF	
Turn-on Delay Time	$t_{d(on)}$		14	28	ns	$V_{DD} = 30\text{ V}, I_D = 15\text{ A},$ $V_{GS} = 10\text{ V},$ $R_G = 0\ \Omega$
Rise Time	t_r		4	10	ns	
Turn-off Delay Time	$t_{d(off)}$		30	60	ns	
Fall Time	t_f		4	10	ns	
Total Gate Charge	Q_G		20	30	nC	$V_{DD} = 48\text{ V},$ $V_{GS} = 10\text{ V},$ $I_D = 30\text{ A}$
Gate to Source Charge	Q_{GS}		7		nC	
Gate to Drain Charge	Q_{GD}		4		nC	
Body Diode Forward Voltage *1	$V_{F(S-D)}$		0.9	1.5	V	$I_F = 30\text{ A}, V_{GS} = 0\text{ V}$
Reverse Recovery Time	t_{rr}		30		ns	$I_F = 30\text{ A}, V_{GS} = 0\text{ V},$
Reverse Recovery Charge	Q_{rr}		40		nC	$di/dt = 100\text{ A}/\mu\text{s}$

Note: *1. Pulsed test

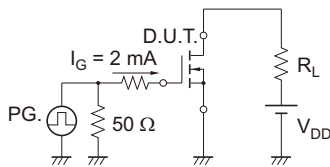
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

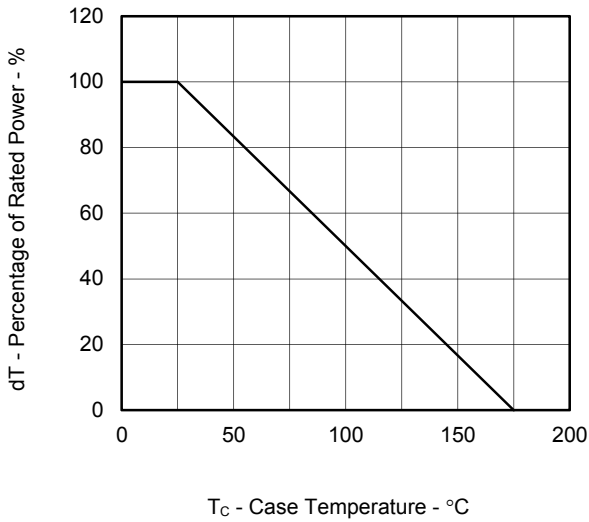


TEST CIRCUIT 3 GATE CHARGE

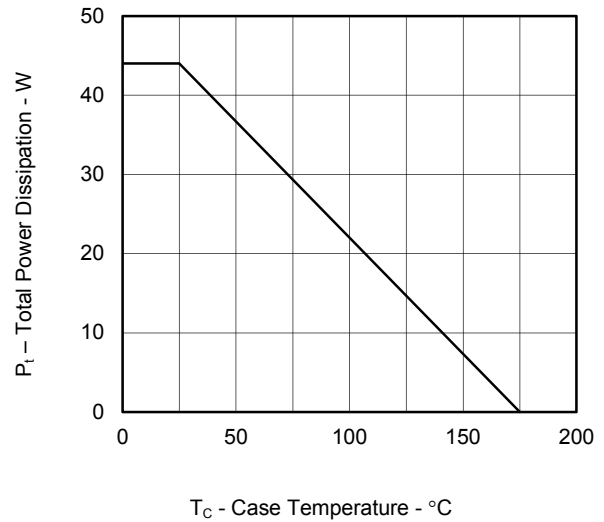


Typical Characteristics (T_A = 25°C)

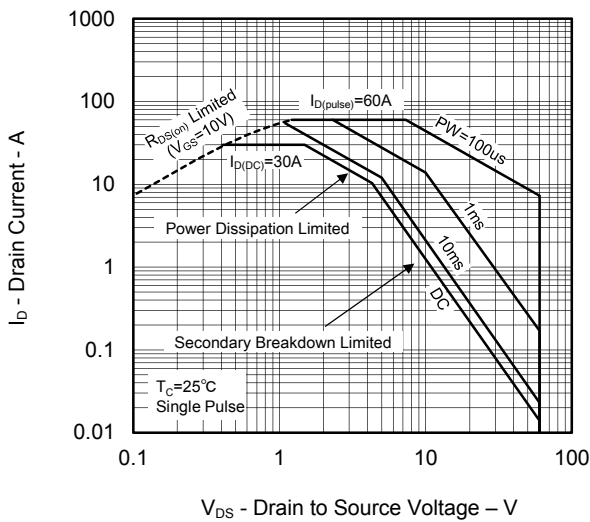
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



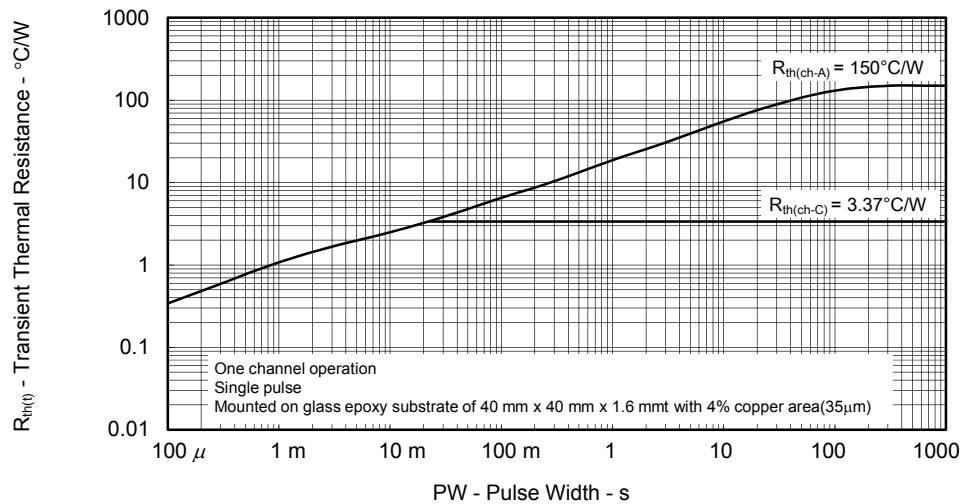
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



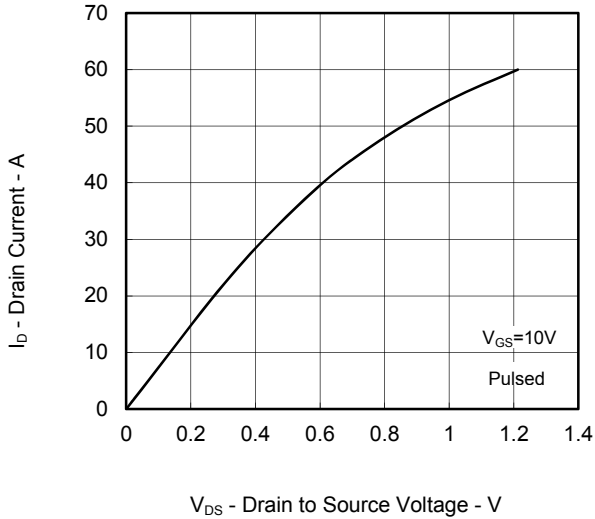
FORWARD BIAS SAFE OPERATING AREA



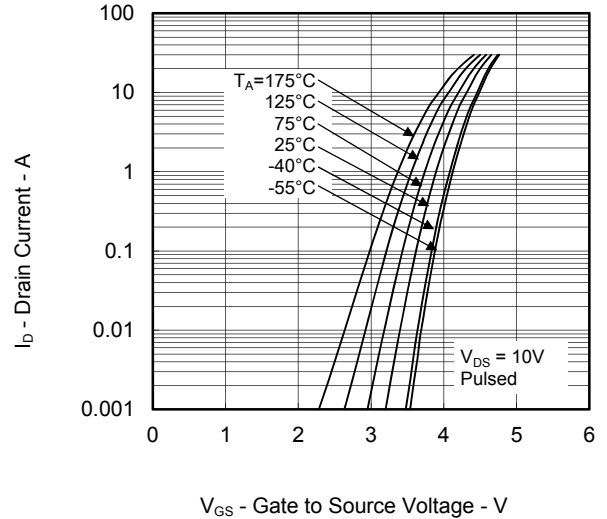
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



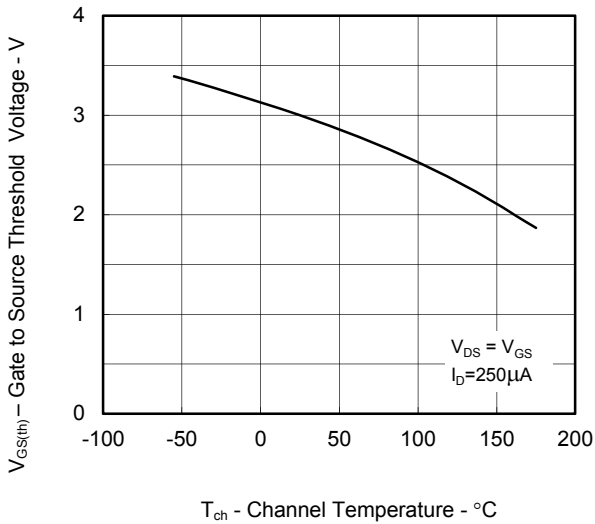
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



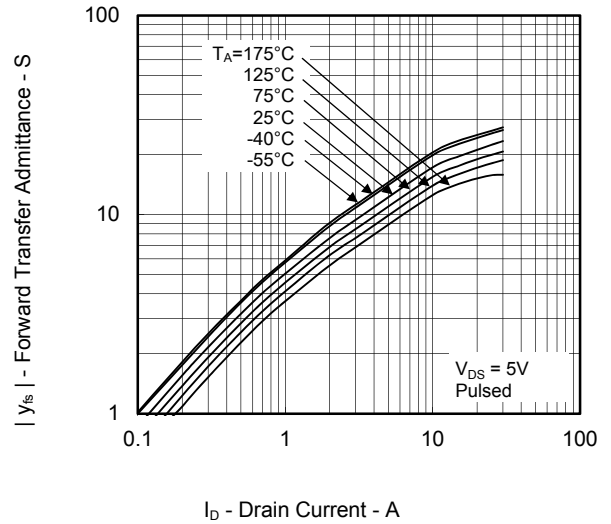
FORWARD TRANSFER CHARACTERISTICS



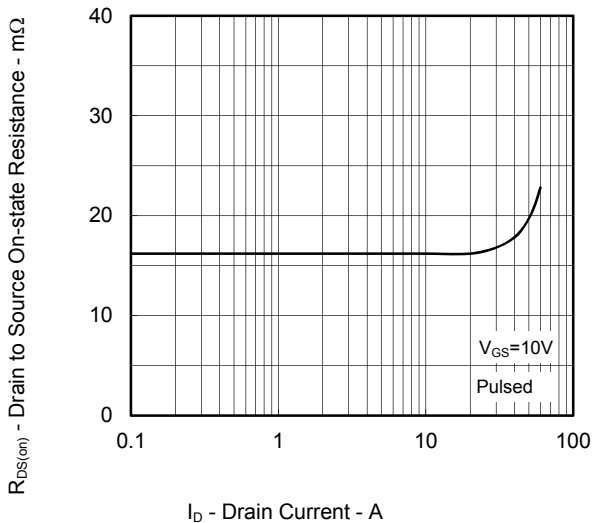
GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE



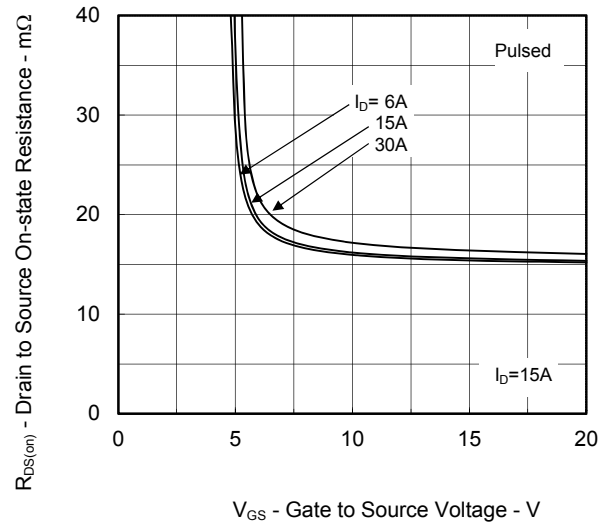
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



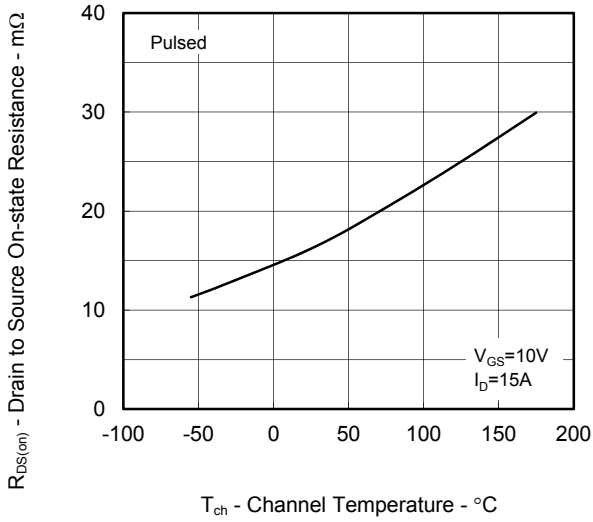
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



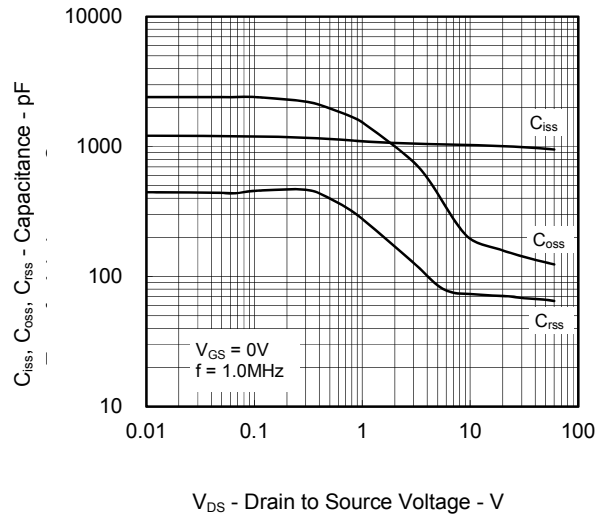
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



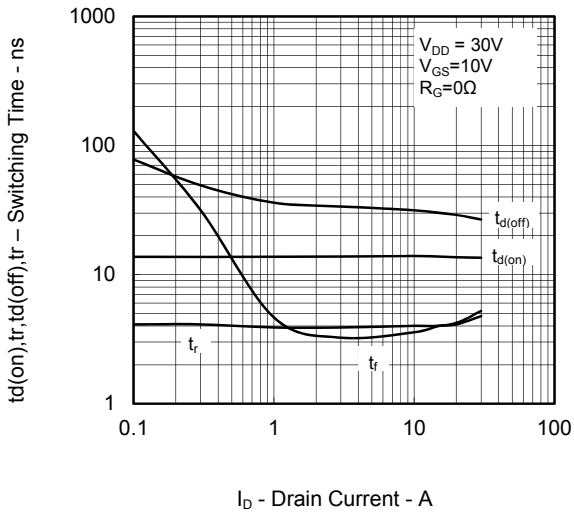
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



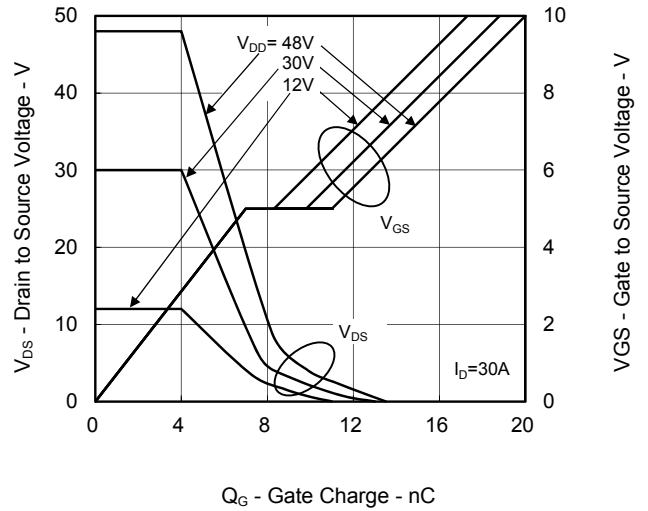
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



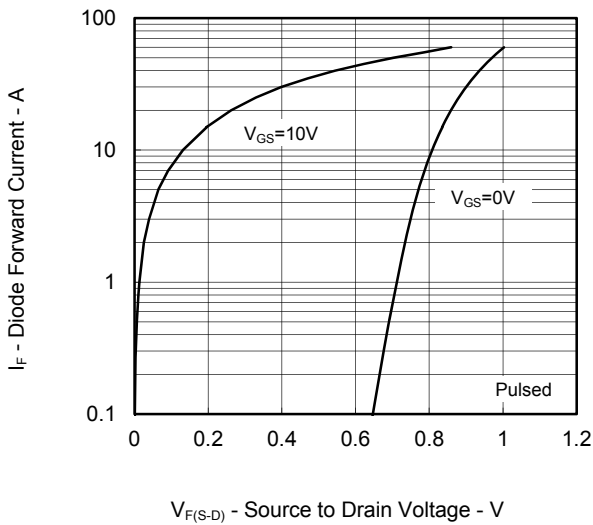
SWITCHING CHARACTERISTICS



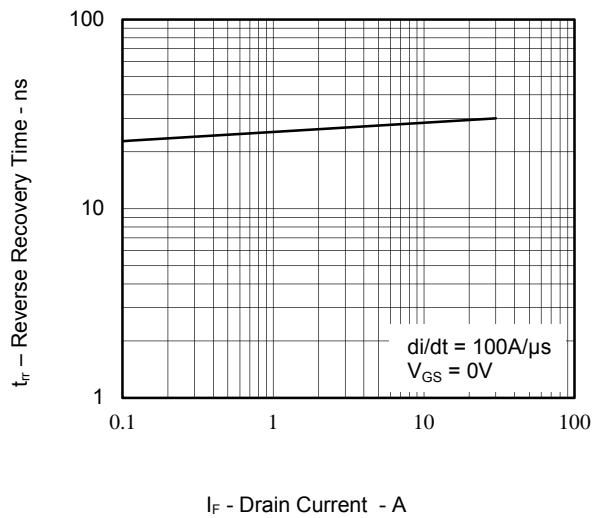
DYNAMIC INPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



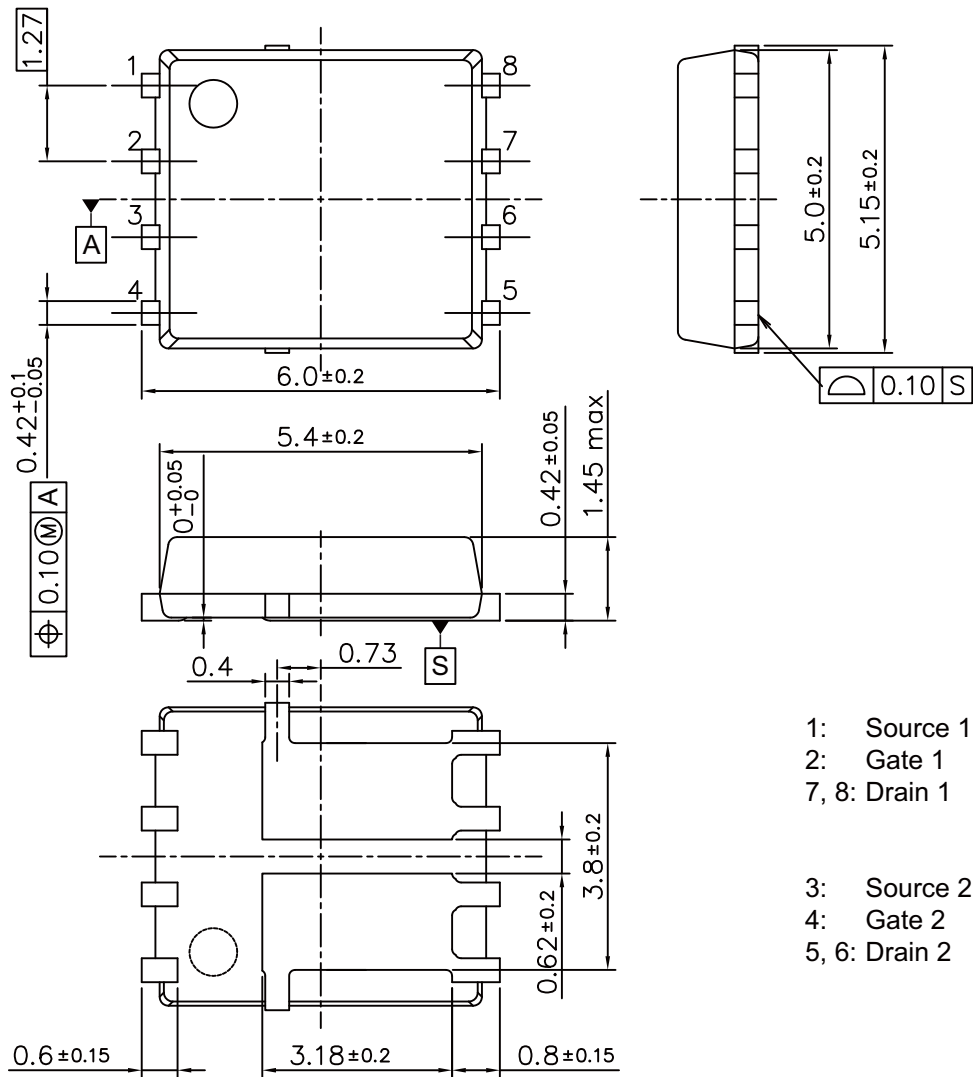
REVERSE RECOVERY TIME vs. DRAIN CURRENT



Package Drawings (Unit: mm)

8-pin HSON Dual (Mass: 0.12 g TYP.)

Renesas package code: PLSN0008DA-A



Revision History	NP29N06QUK Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	Mar 28, 2016	—	First Edition Issued

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